

Serial No. 09/532,892
Docket No. 00USFP465-M.K.

4

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Attorney's Deposit Account No. 50-0481.

Respectfully Submitted,

Date: 5/13/02

Peter A. Balnave
Peter A. Balnave
Reg. No. 46,199

McGinn & Gibb, PLLC
8321 Old Courthouse Rd. Suite 200
Vienna, VA 22182-3817
(703) 761-4100
Customer No. 21254

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Twice Amended) A semiconductor memory device, including a copper fuse section that is oxidized by a laser beam in an oxidizing environment, comprising:
 - a dielectric film including a first film section formed on a substrate, a second film section formed on said first film section, and a third film section formed over said second film section;
 - a wiring line structure, [includingz] including:
 - a first and a second wiring line, each of said first and second wiring lines formed [on] directly upon said second film section of said dielectric film without an intervening film therebetween and extending in an opposite direction, and
 - said copper fuse section formed on said first film section of said dielectric film, an end of said copper fuse section being connected to said first wiring line without an intervening film therebetween and another end of said copper fuse section being connected to said second wiring line without an intervening film therebetween; and
 - an opening formed in said third and second film sections of said dielectric film and between said first and second wiring lines, wherein said opening provides access to said laser beam to oxidize said copper fuse section in said oxidizing environment.